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Erratum

Atom probe tomography of phosphorus- and boron-doped silicon nanocrystals with various compositions of silicon rich oxide — ERRATUM

Keita Nomoto, Sebastian Gutsch, Anna V. Ceguerra, Andrew Breen, Hiroshi Sugimoto, Minoru Fujii, Ivan Perez-Wurfl, Simon P. Ringer, and **Gavin Conibeer**

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In Nomoto et al.,[1] on page 291 the wrong distance units were listed regarding the extraction of the P and B concentration in Si NCs and the oxide region. They were listed as “m,” when they should have been listed as “nm.” The sentence therefore should have read:

“The P and B concentration in Si NCs and the oxide region was extracted from the distance around 0.5 nm and −2.5 nm, respectively.”

The publisher regrets this error.

Reference

1. K. Nomoto, S. Gutsch, A.V. Ceguerra, A. Breen, H. Sugimoto, M. Fujii, I. Perez-Wurfl, S.P. Ringer, and G. Conibeer: Atom probe tomography of phosphorus- and boron-doped silicon nanocrystals with various compositions of silicon rich oxide. *MRS Communications* **6**(3), 287–292 (2016). doi: 10.1557/mrc.2016.37.